

RESONANT TRANSPORT THROUGH SEMICONDUCTOR NANOSTRUCTURES

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Transport through semiconductor nanostructures is a quantum-coherent process. This review focuses on systems in which the electron's dynamics is ballistic and the transport is dominated by the scattering from structure boundaries. Opposite to the well-known case of the nuclear reactions, the potentials defining semiconductor structures are nonspherically symmetric and the asymptotic motion of the electrons is determined by the different potential levels in the contacts. For this special type of potential the mathematical foundations for the scattering theoretical description of the transport phenomena are presented. The transport properties of the system are then derived from the scattering matrix using the Landauer-Buttiker formalism. A rigorous analysis of the analytical properties of the S matrix leads to the most general resonant line shape described by a Fano function with a complex asymmetry parameter. On this basis the resonant and nonresonant contributions to the conductance and capacitance of the system are identified.

I. INTRODUCTION

A remarkable feature of the physics of semiconductor materials is the possibility of designing and manufacturing artificial structures in which the electrons can be confined in zero, one, and two dimensions¹. The region of confinement, usually called quantum system, is coupled to contacts through tunneling barriers which assure the dominance of the quantum effects in the transport phenomena. Due to the coupling to the electrons in the Fermi sea of each contact the discrete electronic states of the isolated quantum system become resonant states². They are special states of the continuum spectrum associated with a maximum of nonzero width of the electronic probability distribution density. The resonance width reflects the open character of the quantum system in semiconductor nanostructures and gives a measure of the coupling strength between the quantum system and contacts. The resonances can be directly seen in the transport properties of nanostructures giving reason to call the transport through this special type of mesoscopic structures as resonant¹.

In 1970 Easki and Tsu³ have proposed for the first time a semiconductor structure where electronic transport proceeds via a resonant tunneling process and after that in 1973 they have also proposed a model⁴ to calculate the current density through the considered system. These were the first steps which have opened an extremely rich field for basic and applied research. The resonant transport has been investigated in a multitude of different mesoscopic semiconductor systems^{1,5,6}: two dimensional electron gas, quantum point contacts, quantum wires and quantum dots. Many phenomena such as universal conductance fluctuations⁷,

the Aharonov-Bohm oscillations⁸, the quantum Hall effect⁹, the quantized conductance in ballistic point contacts¹⁰, Coulomb blockade oscillations¹¹, chaotic dynamics in quantum dots¹², and Kondo effect in single electron transistors¹³, have been observed and discussed in the well-known theory pioneered by Landauer and Buttiker^{14,15}. The widely successful application of this formalism shows that electron transport through a mesoscopic system is quite similar to scattering in nuclear or atomic physics¹⁶. The most important difference is that for transport the asymptotic motion of the electrons is determined by the different potential levels in the contacts and therefore is not free as in the nuclear reaction theory. In turn, the spherical symmetry of the problem is broken and the methods to solve the scattering problem cannot be directly imported from the theory of nuclear reactions. The peculiarities of the scattering potential require a new theoretical description of the scattering phenomena appropriate for the transport. In this theory not only the values of the potential in the contacts should be taken into consideration, but also the strength of the coupling between the quantum system and the contacts. Recent research on Fano resonances in the conductance of a single electron transistor¹⁷, on fluctuations of the local density of states in the emitter¹⁸ and on Luttinger liquid behavior in ballistic transport through quantum wires¹⁹, has established the importance of the interaction of the quantum system with the contacts. As an effect of this interaction the line shape of the resonant profile is asymmetric and cannot be described by the common Wigner-Breit distribution anymore.

The main aim of this paper is to present the mathematical foundations for the scattering theoretical description of coherent transport phenomena and to describe the relevant resonances for the transport properties. The paper is structured as follows: Sec. II presents the method to determine the scattering matrix and the scattering functions associated to the scattering potential of the nanostructure. In the second part of this section the electronic charge and current densities are deduced in the frame of the Landauer-Buttiker formalism using the second quantization technique. Sec. III presents an analytical theory of the quasi-isolated transport resonances, and the signature of these resonances in the conductance and capacitance measurements performed on semiconductor nanostructures is identified. The Fano functions with a complex asymmetry parameter arise as the most general resonant line shape and we provide explicit expressions for the parameters of the Fano profile.

II. SCATTERING APPROACH TO QUANTUM TRANSPORT

A. THE CONSIDERED SYSTEM TYPE

The wave function which describes the electronic state of energy E is a solution of the Schrodinger equation

$$\frac{1}{2m} \mathbf{P}^2 + V_{\text{eff}}(\mathbf{r}) = E \quad (E; \mathbf{r}) = 0; \quad (1)$$

where \mathbf{P} is the momentum operator, $V_{\text{eff}}(\mathbf{r})$ is the effective potential energy which is a sum of the heterojunction conduction band discontinuities, the electrostatic potential due to the ionized donors and acceptors, the self-consistent Hartree and exchange potentials due to free carriers and external potentials. The electronic states in mesoscopic systems are easily described within the effective mass approximation whose validity requires that the envelope function $(E; \mathbf{r})$ be slowly varying over dimensions comparable to the unit cell of the crystal²⁰.

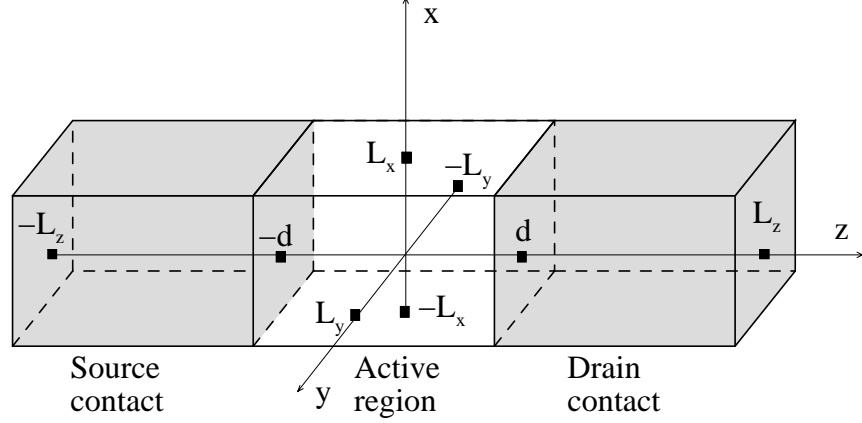


FIG. 1: A system relevant for transport properties: active region with size $2d$ sandwiched between source and drain contacts. The dimensions of the system are large enough to be extended to infinity ($d \ll L_x, L_y, L_z$).

We restrict our analysis to the case of semiconductor nanostructures presented schematically in Fig. 1, in which the current flows only in one direction, from the source to the drain contact, called transport direction; any kind of residual current is neglected. This means that the electrons are either bound in the lateral directions or freely moving in a plane perpendicular to the transport direction, so that the mean value of the lateral current is zero. Consequently, the potential energy in which the electrons move should have a perpendicular component $V_\perp(\mathbf{r})$, which we assume independent of the coordinate in the transport direction, i.e. $V_\perp(\mathbf{r}) = V_\perp(\mathbf{r}_\perp)$. For the structures which contain only a 2DEG and no lateral modulation $V_\perp(\mathbf{r}_\perp) = 0$, whereas for quantum dots $V_\perp(\mathbf{r}_\perp)$ is considered either a parabolic or a square infinite well potential energy. We assume, also, that except for this overall component $V_\perp(\mathbf{r}_\perp)$, there is no other lateral potential which can supplementary confine the electrons in a certain region of the structure. Thus, the potential energy is separable,

$$V_{\text{eff}}(\mathbf{r}) = V(z) + V_\perp(\mathbf{r}_\perp): \quad (2)$$

This special form of $V_{\text{eff}}(\mathbf{r})$ seems to be a strong restriction and it is not easy to imagine its validity for structures with complex geometry, such as a single electron transistor¹⁷, but it is the price paid for a good analytical description of the transport phenomena in semiconductor nanostructures.

Due to the separable form of the potential, a particular solution of the Schrodinger equation (1) associated to the energy $E = E_\perp + \epsilon$ is

$$\psi^{(s)}(E; \mathbf{r}) = \phi(\mathbf{r}_\perp) \psi^{(s)}(\epsilon; z); \quad (3)$$

where ϵ indexes the energy levels E_\perp associated with the motion in the lateral directions. Here s is the degeneracy index for the electron motion in the transport direction. The functions $\phi(\mathbf{r}_\perp)$ and the energies E_\perp are the solutions of the eigenvalue problem

$$\frac{1}{2m} \mathbf{p}_\perp^2 + V_\perp(\mathbf{r}_\perp) \phi(\mathbf{r}_\perp) = E_\perp \phi(\mathbf{r}_\perp): \quad (4)$$

The Hamilton operator of this problem is a Hermitian one and, consequently, the eigenfunction set $\{\psi_n(\mathbf{r})\}$ forms a basis for which the orthogonality and completeness relations

$$\int_V d\mathbf{r} \psi_n(\mathbf{r}) \psi_m^*(\mathbf{r}) = \delta_{nm};$$

$$\sum_n \psi_n(\mathbf{r}) \psi_n^*(\mathbf{r}') = \delta(\mathbf{r} - \mathbf{r}'); \quad (5)$$

are valid. The index n is generic; for a free electron system in a plane perpendicular to the transport direction this index should be replaced by a 2D wave vector \mathbf{k}_\parallel . The energy spectrum becomes continuous ($E_\parallel = \hbar^2 k_\parallel^2 / 2m$). Thus, in Eqs. (5) ψ_n is transformed into $\psi_{\mathbf{k}_\parallel}$ and the sum over n becomes an integral over \mathbf{k}_\parallel ($\int \frac{A}{(2\pi)^2} d\mathbf{k}_\parallel$, where A is the lateral area of the system). Every energy level E_\parallel is degenerate with an infinite degeneracy. In the opposite limit, for a complete confinement of the system in the lateral directions, the energy levels are discrete and nondegenerate, and n is substituted by a quantum number.

The z -dependent function in Eq. (3) is a solution to the one dimensional eigenvalue problem

$$\left[-\frac{\hbar^2}{2m} \frac{d^2}{dz^2} + V(z) \right] \psi(z) = E_\parallel \psi(z); \quad (6)$$

For nanostructures, the potential energy $V(z)$ has some common properties: There is an active region which is small at the scale of the whole system. Inside this region, the electrons are elastically scattered from interfaces between different layers or between allowed and not allowed (depletion) domains in the case of a structured 2DEG. This region is also called scattering region and it is embedded between two contacts, which are practically semi-infinite homogeneous semiconductors. The electrons inside the contact regions move in a potential energy given only by the bulk conduction band structure. A relation between the surfaces of the scattering region and the interfaces between heterostructure layers or domains of the 2DEG can not be established. Each interface can cause elastic scattering and should be included in the scattering region. Thus, the planes $z = \pm d$ are chosen inside the homogeneous materials of the contacts, far enough from any interface and, of course, the choice is not unique. From the mathematical point of view, the potential energy $V(z)$ is a function which varies considerably over small distances inside the scattering region and is constant outside, i.e. $V(z < -d) = V_1$ and $V(z > d) = V_2$, where $\pm d$ are the limits of the scattering region. Further we introduce the notations: $V_m = \min(V_1; V_2)$ and $V_M = \max(V_1; V_2)$.

B. S-MATRIX AND SCATTERING STATES

The above considerations about the potential energy experienced by the electrons allow us to reduce the Schrodinger equation (1) to the effectively one dimensional eigenvalue problem (6). This problem is essentially a scattering problem for a particle with mass m , in a potential with nonspherical symmetry, and it is usually solved in the scattering matrix approach¹⁴.

In the stationary description of the scattering process it is assumed that the wave function of the system at large distances from the scattering region is a superposition of an incident-

and a scattered wave²¹. In our case the electrons are elastically scattered inside the domain $[-d; d]$ and for all points outside this region the z -dependent part of the wave function is given by

$$\psi(z) = \begin{cases} \psi_{in}^{(1)}(k_1; -d) \exp[ik_1(z+d)] + \psi_{out}^{(1)}(k_1; -d) \exp[-ik_1(z+d)]; & z < -d \\ \psi_{in}^{(2)}(k_2; d) \exp[-ik_2(z-d)] + \psi_{out}^{(2)}(k_2; d) \exp[ik_2(z-d)]; & z > d \end{cases} \quad (7)$$

where $\psi_{in=out}^{(s)}(k_s; d)$ are complex coefficients and

$$k_s(\epsilon) = \sqrt{\frac{2m}{\hbar^2} (\epsilon - V_s)}; \quad s = 1, 2 \quad (8)$$

If $\epsilon > V_s$, then k_s is a nonzero positive number according to the definition of the real square root function. However, if $\epsilon < V_s$, we have to take the first branch of the complex square root function, so that $k_s = i|k_s|$. At this stage we would like to point out the main difference between a spherically symmetric scattering problem like in the nuclear physics and a transport scattering problem: in the former only one wave vector for every value of the total energy is defined, while in the latter there are two wave vectors, k_s , $s = 1, 2$, for each energy associated with the electron motion in the transport direction. If the materials of the source and drain contacts are different or when a current flows through the structure, V_1 and V_2 are different and consequently $k_1 \neq k_2$.

For a fixed energy there are at most two independent solutions of Eq. (6) and, consequently, at most two expansion coefficients $\psi_{in=out}^{(s)}(k_s; d)$ can be independent. We choose them $\psi_{in}^{(1)}(k_1; -d)$. The coefficients corresponding to the outgoing waves in Eq. (7) should be expressed in terms of $\psi_{in}^{(1)}(k_1; -d)$,

$$\begin{pmatrix} \psi_{out}^{(1)}(k_1; -d) \\ \psi_{out}^{(2)}(k_2; d) \end{pmatrix} = S(\epsilon) \begin{pmatrix} \psi_{in}^{(1)}(k_1; -d) \\ \psi_{in}^{(2)}(k_2; d) \end{pmatrix} \quad (9)$$

The matrix $S(\epsilon)$, defined for every value of the energy associated with the motion of the electron in the transport direction, contains all the information about the collisions in the system²¹ and is called scattering matrix. As a consequence of the existence of two wave vectors for each value of the energy the scattering processes are described by a 2×2 matrix even in the simplest case.

For energies smaller than the absolute minimum of the potential energy, the solution given by Eq. (7) should be zero and $\psi_{in=out}^{(s)}(k_s; d) = 0$. If the energies are greater than $\min[V(z)]$, the eigenvalue spectrum of the one dimensional Schrodinger equation (6) has a discrete part for $V_m > \epsilon > \min[V(z)]$ associated with bound states and a continuous part for $\epsilon > V_m$ corresponding to the scattering states. We are interested in describing elastic processes which contribute to the transport phenomena and in this case the bound states do not play any role; Further we assume $V(z) = V_m$. The continuous part of the energy spectrum has two important regions: $V_m < \epsilon < V_m$, for which two independent solutions of Eq. (6) exist, and $V_m = \epsilon = V_m$ with only one solution. For the degenerate energy levels there is not an unique way of defining the eigenfunctions and we further prefer to use the so called

scattering functions¹⁴,

$$\psi^{(1)}(z) = \frac{1}{2} \begin{cases} \exp[ik_1(z+d)] + S_{11}(E) \exp[-ik_1(z+d)]; & z < -d \\ S_{21}(E) \exp[ik_2(z-d)]; & z > d \end{cases}; \quad (10)$$

$$\psi^{(2)}(z) = \frac{1}{2} \begin{cases} S_{12}(E) \exp[-ik_1(z+d)]; & z < -d \\ \exp[-ik_2(z-d)] + S_{22}(E) \exp[ik_2(z-d)]; & z > d \end{cases}; \quad (11)$$

$\psi^{(1)}(z)$ corresponds to a particle which comes into the scattering system from the left reservoir ($s = 1$) and is either transmitted or reflected. We can identify the element $S_{11}(E)$ of the S matrix with the reflection amplitude, $r^{(1)}(E)$, and the element $S_{21}(E)$ with the transmission amplitude, $t^{(1)}(E)$. $\psi^{(2)}(z)$ corresponds to a particle coming from the right side of the system ($s = 2$). The reflection and transmission amplitudes for this particle are $r^{(2)}(E) = S_{22}(E)$ and $t^{(2)}(E) = S_{12}(E)$, respectively. In the case $E < V$, the time translation invariance requires that $j^{(s)}(E) = 1, s = 1, 2$.

The step functions

$$\theta(E) = \begin{cases} 1; & E > V_s \\ 0; & E < V_s \end{cases}; \quad s = 1, 2; \quad (12)$$

ensure that for $V_m < E < V$ there is only one scattering function for each energy E .

Generally, the wave functions are solutions of a differential equation and are defined up to a constant factor. In the above expression, we fix this constant, so that, in the limit of free particles [$V(z) \rightarrow 0, d \rightarrow 0$], the scattering functions [Eqs. (10-11)] become eigenfunctions of the momentum operator P_z .

The matrix elements of S , i.e. the transmission and reflection coefficients, are formally determined by the continuity conditions of the scattering functions and their first derivatives at $z = \pm d$,

$$\psi(E) = \frac{1}{2} [\psi(E) [1 + S(E)]] \quad (13)$$

with the matrices $(S(E))_{ss^0} = (S^{(s)}(E; (-1)^s d))$ and $S_{ss^0} = (S(E))_{ss^0}, s; s^0 = 1, 2$, and

$$K_s(E) = \frac{i}{2} \frac{1}{2d} (\psi(E)) K(E) [1 - S(E)] \quad (14)$$

with $(K_s(E))_{ss^0} = (-1)^s \frac{\partial \psi^{(s)}(E)}{\partial z} \bigg|_{z=(-1)^s d}$ and $K_{ss^0} = k_s(E) = (E - V_s)/2d, s; s^0 = 1, 2$, respectively.

We can use these conditions only after the calculation of the scattering functions inside the scattering region.

In case of a general potential inside the scattering region, we can not represent the functions $\psi^{(s)}(z)$ by elementary functions between $-d$ and d and it is necessary to expand them into a basis of eigenfunctions of a solvable problem. In the R matrix formalism the Wigner-Eisenbud basis is considered, i.e. the eigenbasis of the Hamilton operator corresponding to the closed counterpart of the studied scattering problem,

$$\frac{\hbar^2}{2m} \frac{d^2}{dz^2} \psi + V(z) \psi = E \psi \quad (15)$$

with the boundary conditions $\psi_l(z) = 0$ at $z = \pm d$. $\psi_l(z)$ are real functions defined only for $z \in [-d; d]$ and verify the orthogonality and the completeness relations,

$$\int_{-d}^d \psi_l(z) \psi_{l'}(z) dz = \delta_{ll'}; \quad (16)$$

$$\sum_{l=1}^{\infty} \psi_l(z) \psi_l(z') = \delta(z - z'); \quad (17)$$

respectively. The R matrix method developed by Wigner and Eisenbud²² and intensively used in the nuclear reaction theory²³, has become important in the last ten years also for describing transport phenomena²⁴.

We expand the wave functions inside the scattering region, $z \in [-d; d]$, in terms of the Wigner-Eisenbud functions

$$\psi_l^{(s)}(z) = \sum_{l=1}^{\infty} a_l^{(s)} \psi_l(z) \quad (18)$$

and the expansion coefficients $a_l^{(s)}$ are given by

$$a_l^{(s)} = \int_{-d}^d \psi_l(z) \psi_l^{(s)}(z) dz \quad (19)$$

for each $s = 1, 2$ and $l = 1$. To determine $a_l^{(s)}$ we use the Schrodinger equation (6) and Eq. (15) satisfied by the Wigner-Eisenbud functions. We multiply them by $\psi_l(z)$ and $\psi_l^{(s)}(z)$, respectively, and the difference between the resulting equations is integrated over the interval $[-d; d]$. Performing an integration by parts in the kinetic energy term and identifying the integral on the right side with the coefficient $a_l^{(s)}$, defined by (19), we obtain

$$a_l^{(s)} = \frac{\hbar^2}{2m} \frac{\psi_l(-d) \frac{\partial \psi_l^{(s)}}{\partial z} \bigg|_{z=-d} - \psi_l(d) \frac{\partial \psi_l^{(s)}}{\partial z} \bigg|_{z=d}}{\psi_l(d) \frac{\partial \psi_l}{\partial z} \bigg|_{z=d} - \psi_l(-d) \frac{\partial \psi_l}{\partial z} \bigg|_{z=-d}}; \quad (20)$$

Inserting Eq. (20) into Eq. (18) we obtain the expression of the scattering functions between $-d$ and d as a function of their derivatives at the edges of the scattering area,

$$\psi_l^{(s)}(z) = \frac{2d}{\hbar^2} \left[R_l^{(s)}(z) \frac{\partial \psi_l^{(s)}}{\partial z} \bigg|_{z=-d} - R_l^{(s)}(z) \frac{\partial \psi_l^{(s)}}{\partial z} \bigg|_{z=d} \right]; \quad (21)$$

where the R function is defined as

$$R_l^{(s)}(z) = \frac{\hbar^2}{2m} \frac{\sum_{l=1}^{\infty} \psi_l(z) \psi_l(z')}{\psi_l(z') \psi_l(z)}; \quad (22)$$

The above expression of the R function has the advantage of being dimensionless. Together with the continuity condition (14) the relation (21) gives the scattering functions inside the scattering region ($-d < z < d$) in terms of the S matrix,

$$\psi_l^{(1)}(z) = \frac{1}{2} \frac{\hbar^2}{m} \frac{2d}{\hbar^2} f_{ik_1} [1 - S_{11}(k_1)] R_l^{(1)}(z) + \frac{1}{2} \frac{\hbar^2}{m} \frac{2d}{\hbar^2} S_{21}(k_1) R_l^{(2)}(z); \quad (23)$$

$$\psi_l^{(2)}(z) = \frac{1}{2} \frac{\hbar^2}{m} \frac{2d}{\hbar^2} f_{ik_1} S_{12}(k_1) R_l^{(1)}(z) + \frac{1}{2} \frac{\hbar^2}{m} \frac{2d}{\hbar^2} [1 - S_{22}(k_1)] R_l^{(2)}(z); \quad (24)$$

The values of the scattering functions on the surface of the scattering domain are then given by

$$(\mathbf{r}) = \frac{i}{2} (\mathbf{r}) R(\mathbf{r}) K(\mathbf{r}) [1 - S(\mathbf{r})]; \quad (25)$$

with the R matrix defined as

$$R(\mathbf{r}) = \begin{pmatrix} R(\mathbf{r}; d; d) & R(\mathbf{r}; d; d) \\ R(\mathbf{r}; d; d) & R(\mathbf{r}; d; d) \end{pmatrix}. \quad (26)$$

The scattering functions are continuous at the edges of the scattering system and we exploit this condition to determine the relation between the R and the S matrix. Equating the two expressions (13) and (25) of the matrix we infer

$$S(\mathbf{r}) = 1 - 2 [1 + iR(\mathbf{r})K(\mathbf{r})]^{-1} \quad (27)$$

for each value of the energy in the domain of the scattering states. For $V_m < \epsilon < V_M$ the above relation can only be used to calculate the matrix elements S_{1s} and S_{2s} with s satisfying the condition $\epsilon > V_s$, $s = 1; 2$. Using Eq. (27) the elements of the scattering matrix can be effectively determined in terms of Wigner-Eisenbud functions and energies. Furthermore, the scattering functions, Eqs. (10-11) and (23-24), can be evaluated in every point of the system, even inside the scattering system.

As shown in the first part of this section, the elements of the S matrix defined by Eq. (9) are in fact the reflection and transmission amplitudes for the particles coming from the left and from the right side of the system. However, for describing transport phenomena in semiconductors in the frame of the Landauer-Buttiker formalism¹⁴, the reflection and transmission probabilities, $R^{(1)}(\epsilon) = r^{(1)}(\epsilon)^2$, $R^{(2)}(\epsilon) = r^{(2)}(\epsilon)^2$, $T^{(1)}(\epsilon) = t^{(1)}(\epsilon)^2$ and $T^{(2)}(\epsilon) = t^{(2)}(\epsilon)^2$, play a central role. We introduce further the current scattering matrix²⁴

$$S(\epsilon) = K^{1=2}(\epsilon) S(\epsilon) K^{1=2}(\epsilon); \quad (28)$$

having the property that $S_{11}(\epsilon)^2 = R^{(1)}(\epsilon)$, $S_{12}(\epsilon)^2 = T^{(2)}(\epsilon)$, $S_{21}(\epsilon)^2 = T^{(1)}(\epsilon)$, and $S_{22}(\epsilon)^2 = R^{(2)}(\epsilon)$. The relation (27) between the R and the S matrix can be rewritten into an equivalent form

$$S(\epsilon) = 1 - 2 [1 + i(\epsilon)]^{-1}; \quad (29)$$

where the matrix of rank two is defined as

$$(\epsilon) = K^{1=2}(\epsilon) R(\epsilon) K^{1=2}(\epsilon) = \sum_{l=1}^X \frac{!_l(\epsilon)}{!_1}; \quad (30)$$

with

$$(!_1(\epsilon))_{ss^0} = \frac{\hbar^2}{2m} (k_s k_{s^0})^{1=2} {}_1((1^s d) {}_1((1^{s^0} d); \quad s, s^0 = 1; 2 \quad (31)$$

for all $l = 1$. Per construction S is a symmetrical matrix with real elements in the domain of the scattering states with $k > k_M$. This property leads to the unitarity of the current scattering matrix,

$$S(k) S^\dagger(k) = S^\dagger(k) S(k) = 1; \quad k > k_M; \quad (32)$$

which includes the reciprocity relations, $R^{(1)}(k) = R^{(2)}(k) = R(k)$, $T^{(1)}(k) = T^{(2)}(k) = T(k)$, and the well-known relation of the flux conservation, $R(k) + T(k) = 1$.

The scattering functions $\psi^{(s)}(k; z)$ form an orthogonal and complete system in the case of a potential energy $V(z)$ which does not allow bound states¹⁵. They are eigenfunctions of the Hamilton operator [Eq. (6)] and the selfadjointness of this operator²⁵ allows us to consider the set as complete,

$$\int_{-\infty}^{\infty} dz \psi^{(s)}(k; z) \psi^{(s')}(k; z) = \delta_{ss'} \delta(k - k'); \quad (33)$$

where

$$g_s(k) = \frac{m}{\hbar^2 k_s(k)}; \quad s = 1, 2 \quad (34)$$

defines the 1D density of states. The orthogonality condition is written as

$$\int_{-\infty}^{\infty} dz \psi^{(s)}(k; z) \psi^{(s')}(k; z) = \delta_{ss'} \delta(k - k') = g_s(k) \delta_{ss'} \delta(k - k') \quad (35)$$

as demonstrated in Appendix A.

C. OBSERVABLES

The conduction electrons in a semiconductor are considered as an electron gas embedded in a positively charged medium which maintains the overall charge neutrality of the system. The simplest approximation for the description of an electron gas is to neglect all interactions: the Coulomb interaction of the electrons with each other and the interaction of the electrons with the positive background. Every electron is then independent from other electrons and subject only to external forces. Each state of the system is described by the field operators $\hat{\psi}(x)$ and $\hat{\psi}^\dagger(x)$. Using the eigenbasis of the one-particle Hamiltonian associated with the Schrodinger equation (1), we can represent $\hat{\psi}(x)$ and $\hat{\psi}^\dagger(x)$ in terms of creation and destruction operators for the states $\psi^{(s)}(k; s)$ of the field, $c_s(k)$ and $c_s^\dagger(k)$, respectively. Thus,

$$\hat{\psi}(x) = \sum_{s=1,2} \int_{-\infty}^{\infty} dk g_s(k) \psi^{(s)}(k; x) c_s(k); \quad (36)$$

$$\hat{\psi}^\dagger(x) = \sum_{s=1,2} \int_{-\infty}^{\infty} dk g_s(k) \psi^{(s)}(k; x) c_s^\dagger(k); \quad (37)$$

with the 1D density of states $g_s(k)$, $s = 1, 2$ defined by Eq. (34). The operators $\hat{\psi}(x)$ and $\hat{\psi}^\dagger(x)$ satisfy the fermion type anticommutation relations; consequently the creation and

destruction operators have the following properties¹⁵,

$$\begin{aligned} c_s(\mathbf{r}); c_{s0}^\dagger(\mathbf{r}) &= (\mathbf{r} | \psi_{s0}(\mathbf{r}) \rangle = g_s(\mathbf{r}); \\ c_s(\mathbf{r}); c_{s0}^\dagger(\mathbf{r}) g &= 0; \\ c_s^\dagger(\mathbf{r}); c_{s0}^\dagger(\mathbf{r}) &= 0; \end{aligned} \quad (38)$$

The many-particle Hamiltonian of the electron system without mutual interaction,

$$\hat{H} = \int d\mathbf{r} \psi^\dagger(\mathbf{r}) \left[\frac{1}{2m} \mathbf{p}^2 + V_2(\mathbf{r}) + V(z) \right] \psi(\mathbf{r}); \quad (39)$$

can also be written in terms of creation and destruction operators,

$$\hat{H} = \sum_{\mathbf{s}} \int d\mathbf{r} g(\mathbf{r}) E(\mathbf{r}) c_s^\dagger(\mathbf{r}) c_s(\mathbf{r}); \quad (40)$$

where $E(\mathbf{r}) = E_2 + \dots$ is the energy of the single particle state $(\mathbf{r}; \mathbf{s})$. An eigenvector $|j\rangle$ of the Hamiltonian (40) is completely determined by the occupation numbers $n_s^{(j)}(\mathbf{r})$ of every single particle state $(\mathbf{r}; \mathbf{s})$,

$$|j\rangle = \prod_{(\mathbf{r}; \mathbf{s})} c_s^{n_s^{(j)}(\mathbf{r})} |0\rangle \quad (41)$$

with $c_s^\dagger(\mathbf{r}) c_s(\mathbf{r}) |j\rangle = n_s^{(j)}(\mathbf{r}) |j\rangle$. According to the Pauli principle, at most one particle may occupy any fermion state so that these occupation numbers are restricted to the values 0 and 1.

The eigenvectors of the Hamiltonian, $|j\rangle$, form an orthonormal and complete system of vectors in the Hilbert space and each general state of the isolated electron gas can be given as a superposition of the pure states of \hat{H} . According to the postulates of the statistical mechanics we suppose this superposition of pure states as incoherent²⁶, so that the mean values of the electron charge and current densities in a mixed state are given by

$$\rho(\mathbf{r}) = \frac{e}{2} \text{Tr} \left[\hat{\rho} \psi^\dagger(\mathbf{r}) \psi(\mathbf{r}) \right] \quad (42)$$

and

$$\mathbf{j}(\mathbf{r}) = \frac{2eh}{m} \text{Tr} \left[\hat{\rho} \mathbf{p} \psi^\dagger(\mathbf{r}) \psi(\mathbf{r}) \right]; \quad (43)$$

respectively, where $\hat{\rho}$ is the density matrix, $e = |e|$ is the elementary charge and the factor 2 comes from the spin degeneracy. In the definition of the electronic current density we have taken into account the conventional sign of the current.

In the diagonal representation of the Hamiltonian the density matrix of the isolated system is also diagonal²⁶, $\hat{\rho}_{ij} = p_j \delta_{ij}$, where p_j denotes here the probability of the system for being in the pure state $|j\rangle$ and satisfies the relation $\sum_j p_j = \text{Tr}[\hat{\rho}] = 1$. Inserting Eqs. (36) and (37) of the field operators in definitions (42) and (43) matrix elements such as $\langle j | \psi_s^\dagger(\mathbf{r}) c_{s0}^\dagger(\mathbf{r}) | j \rangle$ occur. The special form of the orthogonality condition for the scattering states [Eq. (35)] yields

$$\langle j | \psi_s^\dagger(\mathbf{r}) c_{s0}^\dagger(\mathbf{r}) | j \rangle = n_s^{(j)}(\mathbf{r}) (\mathbf{r} | \psi_{s0}(\mathbf{r}) \rangle = g_s(\mathbf{r}); \quad (44)$$

Therefore, the electron charge and current densities become

$$q(\mathbf{r}) = -2e \int_{V_s}^{\infty} d\epsilon g(\epsilon) j_z(\mathbf{r}; \epsilon)^2 \rho^{(s)}(\epsilon; z) n_s(\epsilon) \quad (45)$$

and

$$j_z(\mathbf{r}) = \frac{2e\hbar}{m} \int_{V_s}^{\infty} d\epsilon g(\epsilon) \hat{e}_z j_z(\mathbf{r}; \epsilon)^2 \text{Im} \left[\rho^{(s)}(\epsilon; z) \frac{\partial \rho^{(s)}(\epsilon; z)}{\partial z} \right] + \rho^{(s)}(\epsilon; z)^2 \text{Im} [(\mathbf{r}_? - \mathbf{r}_?) \cdot (\mathbf{r}_? - \mathbf{r}_?)] n_s(\epsilon); \quad (46)$$

respectively, where $n_s(\epsilon)$ is the mean occupation number of the single particle state $(\epsilon; s)$,

$$n_s(\epsilon) = \text{Tr} [\hat{c}_s^\dagger(\epsilon) \hat{c}_s(\epsilon)] \quad (47)$$

and \hat{e}_z is the unity vector of the z axis.

Further we analyze the component of the current density on the transport direction. Replacing in Eq. (46) the scattering function by their expressions (10) and (11), and $g_s(\epsilon)$ by Eq. (34) we find

$$j_z(\mathbf{r}; z) = \frac{2e\hbar}{h} \int_{V_M}^{\infty} d\epsilon j_z(\mathbf{r}; \epsilon)^2 \left[n_1(\epsilon) |S_{11}(\epsilon)|^2 + n_2(\epsilon) |S_{21}(\epsilon)|^2 \right] \quad (48)$$

in the source contact region ($z < -d$) and

$$j_z(\mathbf{r}; z) = \frac{2e\hbar}{h} \int_{V_M}^{\infty} d\epsilon j_z(\mathbf{r}; \epsilon)^2 \left[n_1(\epsilon) |S_{12}(\epsilon)|^2 + n_2(\epsilon) |S_{22}(\epsilon)|^2 \right] \quad (49)$$

in the drain contact region ($z > d$). The nondegenerate energy levels between V_m and V_M do not contribute to the current because on the one side of the scattering region the corresponding scattering functions decay exponentially and on the other side the reflection coefficient is 1. For $\epsilon > V_M$ the current scattering matrix $S(\epsilon)$ is a unitary matrix and in turn the component of the current density in the transport direction can be written as

$$j_z(\mathbf{r}; z) = \frac{2e\hbar}{h} \int_{V_M}^{\infty} d\epsilon T(\epsilon) [n_1(\epsilon) - n_2(\epsilon)]; \quad |z| > d \quad (50)$$

where $T(\epsilon)$ is the transmission probability. The current density is actually independent on z in the contact regions and has the same value in the source and drain contacts proving the current conservation through the system.

To calculate the mean value of the occupation number $n_s(\epsilon)$ of the single particle state $(\epsilon; s)$ we need some considerations about the conduction electrons in nanostructures. The electron gas analyzed above extends in fact only in a domain whose dimensions are comparable with the phase coherence length of the nanostructure and are larger than the size of the scattering region. The rest of the heterostructure is usually a highly doped semiconductor or a metal and acts as a particle and energy reservoir for the considered electron gas. If the phase coherence length is large enough so that the electron gas can be taken as a macroscopic system, the particle number and the energy of this system are practically constant in

the limit of thermodynamic equilibrium. That means that the electron gas is quasi-isolated and the above expressions for the charge and current densities remain valid. The advantage of considering the system of electrons in contact with a particle- and energy bath is that the mean value of the occupation number is given by the Fermi-Dirac distribution function²⁶,

$$n_s(\epsilon) = f_{FD}(\epsilon + E_F); \quad (51)$$

where ϵ is the chemical potential of the system at thermodynamic equilibrium, fixed by the doping in the contact regions of the heterostructure. The expression (51) of the mean value of the occupation number assures that the current is zero at thermodynamic equilibrium.

D. LANDAUER-BUTTIKER FORMALISM

To calculate the transport properties in the Landauer-Buttiker formalism¹⁴, electrons can be thought of as two noninteracting Fermi-gases: First, the electrons coming from the source contact which occupy the single-particle scattering states with $s = 1$ according to the Fermi-Dirac distribution function $f_{FD}(\epsilon + E_F)$,

$$n_1(\epsilon) = f_{FD}(\epsilon + E_F); \quad (52)$$

where ϵ is the chemical potential of the source contact. Second, the electrons coming from the drain contact which occupy the single particle states indexed by $s = 2$ according to the Fermi-Dirac distribution function $f_{FD}(\epsilon + E_F)$,

$$n_2(\epsilon) = f_{FD}(\epsilon + E_F); \quad (53)$$

$E_F = \epsilon_1 - eU_{sd}$ being the chemical potential of the drain contact. The potential difference $\epsilon_1 - \epsilon_2$ results from an externally applied drain-source voltage, U_{sd} .

Using these basic assumptions of the Landauer-Buttiker formalism and the normalization condition (5) of the functions $\psi_s(\mathbf{r})$ we determine from Eq. (45) the electronic charge $Q = \int d\mathbf{r} q(\mathbf{r})$ inside the scattering system,

$$Q = \frac{2em}{h^2} \sum_s \int_{v_s}^{\infty} d\epsilon \frac{P_s(\epsilon)}{k_s(\epsilon)} f_{FD}(\epsilon + E_F); \quad (54)$$

where

$$P_s(\epsilon) = \int_{-\infty}^{\infty} dz |\psi_s(\mathbf{r}; z)|^2 \quad (55)$$

is the particle probability distribution. For a free electron system in a plane perpendicular to the transport direction index s should be replaced by a 2D wave vector \mathbf{k}_s and the electron charge in the scattering region becomes

$$Q = \frac{e}{A} \frac{m}{h^2} \sum_s \int_{v_s}^{\infty} d\epsilon \frac{P_s(\epsilon)}{k_s(\epsilon)} dE f_{FD}(\epsilon + E_F); \quad (56)$$

where E denotes the total energy of the electron and A is the lateral area of the system. It is the great advantage of using the R-matrix formalism to enable the analytical calculation

of $P_s(\epsilon)$ inside the scattering system, as shown in Appendix A. Its expression is given by Eq. (A 7) and using the expressions (13-14) for g_s and S_{ss} we obtain

$$P_s(\epsilon) = \frac{1}{2} \text{Im} \left[\frac{1}{g_s(\epsilon)} S^y(\epsilon) \frac{dS_{ss}(\epsilon)}{d\epsilon} + \frac{S_{ss}(\epsilon)}{k_s(\epsilon)} \right] \quad (57)$$

for $\epsilon > V_M$,

$$P_1(\epsilon) = \frac{1}{2} \text{Im} \left[\frac{1}{g_1(\epsilon)} S_{11}(\epsilon) \frac{dS_{11}(\epsilon)}{d\epsilon} + \frac{S_{11}(\epsilon)}{k_1(\epsilon)} \frac{1}{4} \frac{k_1(\epsilon)}{[k_2(\epsilon)]^2} S_{21}(\epsilon)^2 \right] \quad (58)$$

for $\epsilon < V_M$ in the case $V_1 < V_2$, and

$$P_2(\epsilon) = \frac{1}{2} \text{Im} \left[\frac{1}{g_2(\epsilon)} S_{22}(\epsilon) \frac{dS_{22}(\epsilon)}{d\epsilon} + \frac{S_{22}(\epsilon)}{k_2(\epsilon)} \frac{1}{4} \frac{k_2(\epsilon)}{[k_1(\epsilon)]^2} S_{12}(\epsilon)^2 \right] \quad (59)$$

for $\epsilon < V_M$ in the case $V_2 < V_1$. The above relations demonstrate that the electronic charge accumulated inside the scattering system is only given by the elements of the scattering matrix.

To describe the transport properties of nanostructures we also need to analyze the current through the system, $I = \int d\mathbf{r}_\perp \mathbf{j}_z(\mathbf{r}_\perp; z)$ as a function of the applied drain-source voltage. Using Eqs. (52-53) we obtain from Eq. (50) the current as

$$I = \frac{2e}{h} \int_{V_M}^{\infty} dE \sum_{\mathbf{k}_\perp} T(\epsilon) [\mathbb{f}_{FD}(\epsilon + E_1) - \mathbb{f}_{FD}(\epsilon + E_2)] \quad (60)$$

for $|\mathbf{j}_\perp| > 0$, where $T(\epsilon)$ is the transmission probability characterizing the scattering region of the system. This is the current between the source and drain contacts. We can also define a current in the lateral directions as results from Eq. (46), but this current is zero for the systems considered in this paper. For the heterostructures with total lateral confinement, the energy levels E_\perp are nondegenerate and the time translational invariance allows us to choose the function $\psi(\mathbf{r}_\perp)$ as real. It results immediately that $\text{Im} [\psi(\mathbf{r}_\perp) \nabla_{\mathbf{r}_\perp} \psi(\mathbf{r}_\perp)] = 0$ and the lateral component of the current density vanishes. In the opposite limit, for a free electron gas in a plane perpendicular to the transport direction we can define a 2D wave vector \mathbf{k}_\perp and $\psi(\mathbf{r}_\perp) = \langle \mathbf{k}_\perp; \mathbf{r}_\perp \rangle = e^{i\mathbf{k}_\perp \cdot \mathbf{r}_\perp} / \sqrt{2}$. It follows in a straightforward manner that $\text{Im} [\psi(\mathbf{r}_\perp) \nabla_{\mathbf{r}_\perp} \psi(\mathbf{r}_\perp)] = \mathbf{k}_\perp / 2$ and the lateral component of the current density becomes zero.

For determining the conductance it is convenient to write the expression (60) of the current into an equivalent form

$$I = \frac{2e}{h} \int_{V_M}^{\infty} dE \sum_{\mathbf{k}_\perp} [\mathbb{f}_{FD}(E + E_1) - \mathbb{f}_{FD}(E + E_2)] T(E + E_1, E + E_2); \quad (61)$$

where the integration is made over the total energy of the electron. This expression has the advantage that it directly yields the conductance. Each energy level E_\perp defines a channel for the electron transport²⁷ and it is usually said that the channels which satisfy the condition $0 < E_\perp < E_F$ are open channels because they contribute to the current. The \mathbb{f} -function in

Eq. (61) serves to remove the channels with exponentially decaying wave functions in the contacts, the so called closed channels for transport. In the linear response regime ($U_{sd} \rightarrow 0$, $V_1 = V_2 \rightarrow 0$) and for low temperatures ($T \rightarrow 0$), we can expand the Fermi-Dirac function $f_{FD}(E - E_2)$ in a Taylor series around E_1 , and thus obtain²⁸ from Eq. (61)

$$G = \frac{2e^2 X}{h} T(E_F - E_2)(E_F - E_2); \quad (62)$$

where $T(\epsilon) = |S_{12}(\epsilon)|^2$ is the transmission probability determined solely by the one-dimensional scattering problem Eq. (6) and E_F is the Fermi energy of the electron gas in the source contact.

III. RESONANCES IN TRANSPORT

The notion of resonances, representing long-lived intermediate states of an open system to which bound states of its closed counterpart are converted due to coupling to continuum, is one of the most fundamental concepts in the domain of quantum scattering². On a formal level resonances show up as poles of the scattering matrix occurring at complex energies $\epsilon_0 = \epsilon_0 - i\Gamma/2$, where ϵ_0 and Γ are called position and width of the resonance, respectively³¹.

The causality condition leads to analytic properties of the scattering matrix when the energy or the wave vector of the electron are extended to complex values³². To calculate the poles of the scattering matrix we exploit these properties which are briefly summarized in the following. $S(\epsilon)$ is a meromorphic function on the two-sheeted Riemann surfaces – one for positive values of the imaginary part of the wave vector and the other for negative values – with a branch point at $\epsilon = 0$ and a cut from 0 to 1 . Bound states poles lie on the negative real axis of the "physical sheet" and, except for them, $S(\epsilon)$ is an analytical function on the physical sheet³³. The resonance poles lie on the second, "unphysical sheet" and come from the possible zeros on the first sheet³². As usually done, we assume these poles to be simple³⁴.

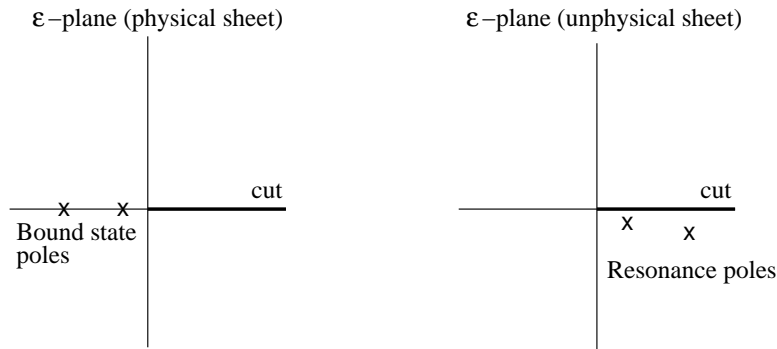


FIG. 2: Left side: "Physical sheet" of the complex energy plane corresponding to the values of the wave vector $k = \sqrt{2m} \sqrt{\epsilon} = \hbar^{-1} \sqrt{2m\epsilon}$ with $\text{Im}[k] > 0$. Poles of the scattering matrix associated with the bound states. Right side: "Unphysical sheet" of the complex energy plane corresponding to the values of the wave vector with $\text{Im}[k] < 0$. Poles of $S(\epsilon)$ associated to resonances.

Our development of the resonance theory starts with the R matrix representation of the S matrix which is particularly well suited to the description of narrow resonances². As demonstrated in Sec. IIB, the two matrices are related to each other through Eq. (29). It is obvious that the resonance poles correspond to the zeros of the denominator function in the expression (29) of the S matrix,

$$\det[1 + i \Gamma(E)] = 0: \quad (63)$$

According to the definition (30) the matrix elements have single poles for each $E = E_n$, $n = 1, 2, \dots$, i.e. for each eigenenergy of the Hamiltonian corresponding to the scattering system isolated from the contacts. The Wigner-Eisenbud energies E_n are real and are associated to the bound states. If the system is coupled to contacts the bound states are transformed into scattering states (at most with a few exceptions depending on the particularities of $V(z)$) and the poles should migrate in the lower part of the "unphysical sheet" of the complex energy plane. Further we demonstrate that the Wigner-Eisenbud energies, E_n , are not solutions of Eq. (63) and therefore they are not singularities of the S matrix. The matrix is split into a resonant part which contains $(E - E_n)^{-1}$ and a regular matrix R ,

$$S(E) = \frac{1}{E - E_n} + \frac{R(E)}{E - E_n} = \frac{1}{E - E_n} + R(E): \quad (64)$$

This decomposition and the property of R to have the determinant zero lead to

$$\det[1 + i \Gamma] = \frac{E(E)}{D(E)} \quad (65)$$

with $E(E) = i \text{Tr}[\Gamma(1 + i \Gamma)^{-1}]$ and $D(E) = \det[1 + i \Gamma]$: Now we can express the S matrix in terms of R and E ,

$$S(E) = \frac{Z(E)}{E(E)}; \quad (66)$$

where the matrix $Z(E)$ is defined as $Z(E) = (1 + i \Gamma)^{-1} \det[1 + i \Gamma] = D(E)$ with $D(E) = \det[1 + i \Gamma]$. In principle, the solutions of the equation $D(E) = 0$ can not be associated with resonance poles of the S matrix. As follows from its definition $E(E)$ becomes infinite for $D(E) \neq 0$. We cannot argue that D and $\det[1 + i \Gamma]$ vanish at the same points and it is convenient to include $D(E)$ in $Z(E)$.

The matrix Z and the function E are related to each other through the unitarity requirement for the S matrix which gives

$$Z Z^\dagger = Z^\dagger Z = E(E)^2; \quad (67)$$

for $E > V_M$.

The representation of the S matrix in Eq. (66) is an exact reformulation of Eq. (29) and has the advantage of directly yielding the equation

$$D(E_0) = 0 \quad (68)$$

to determine the positions $E_0 = E_0 \pm i\Gamma/2$ of the poles in the complex energy plane. It is obvious that Eq. (66) has no singularities for real energies in the interval $(E_1; E_2)$. The coupling to the contacts leads to a nonzero imaginary part of the resonance energy and the stronger the coupling the larger the difference between the Wigner-Eisenbud energy E_0 and the resonant energy E_0 , $\Gamma \propto \Gamma$. Each Wigner-Eisenbud energy was associated a resonance energy.

In the following we analyze the narrow transport resonances for which Γ is a small quantity and the line shape is given by an asymmetric Fano function. Therefore, as a basic assumption for our theory of the resonant Fano line shape, we require the validity of the linearization of E and implicitly Z in a domain of the complex energy plane that includes the pole E_0 and the part of the real axis which contains the transmission peak associated with the resonance, i.e. the resonance domain. To obtain the line shape of the resonance we employ a formal expansion of the S -matrix as given in Eq. (66) in a Laurent series around the pole $E_0 = E_0 \pm i\Gamma/2$ and neglect the derivatives up to the second order of E and Z at the points E_0 and E_0 ^{25,28}. Thus, the S matrix has the form

$$S(E) = \frac{1}{E - E_0 + i\Gamma/2} \left[\frac{Z(E_0)}{1 - \frac{dE}{dZ} \bigg|_{E_0}} + \frac{\frac{dZ}{dE} \bigg|_{E_0}}{1 - \frac{dE}{dZ} \bigg|_{E_0}} \right] \quad (69)$$

Eq. (66) ensures that the S matrix is an analytic function in the resonance domain excepting the pole, condition which is required for the existence of the Laurent series. After the linearization of E in Eq. (68) we find $\frac{dE}{dZ} \bigg|_{E_0} = \frac{E_0}{E_0} = 1$ and $\frac{dZ}{dE} \bigg|_{E_0} = \frac{1}{E_0} = \frac{1}{E_0}$ and then the expression of the S matrix inside the resonance domain becomes

$$S(E) = \frac{S(E_0)}{E - E_0 + i\Gamma/2} + S_{bg} \quad (70)$$

where $e = 2(E - E_0)/\Gamma$ and

$$S_{bg} = \frac{1}{E_0} \frac{dZ}{dE} \bigg|_{E_0} \quad (71)$$

Eq. (70) has a standard form^{32,34,35,36}, but we can provide here an explicit expression for the nonresonant component of the scattering matrix, S_{bg} . The first term in Eq. (70) represents the resonant part of S . For each element of the matrix S it is seen from Eq. (70) that the resonant part undergoes a phase change of π when the energy passes the resonance. In general, this produces a change between constructive and destructive superposition of the resonant and the nonresonant part. Therefore, an asymmetric line is obtained.

The resulting expression (70) preserves the unitarity of the scattering matrix only in linear order Γ ²⁸:

$$SS^\dagger = S^\dagger S = 1 + \frac{\Gamma^2}{e^2 + 1} \quad (72)$$

We expect that our approximation is valid as long as the second term on the right hand side of Eq. (72) is small compared to 1, i.e. the deviation of S from unitarity is small. This way, for each maximum we can estimate the range of validity for our approximation through the requirement $(1 - \Gamma^2/(e^2 + 1)) \approx 1$, $i, j = 1, 2$.

IV . APPLICATIONS

A . CONDUCTANCE THROUGH A QUANTUM DOT

As a first application of our resonance theory of transport we calculate the conductance through a quantum dot embedded in a quantum wire²⁸. The potential energy experienced by electrons has two components: the z -independent lateral confinement potential energy $V_\perp(x_\perp)$, which provides the one-dimensional character of the structure, and $V(z)$ a double barrier potential separating the quantum dot from the rest of the system (Fig. 3).

In the linear response regime ($V_{sd} \rightarrow 0$, $V_1 = V_2 = 0$) and for low temperatures ($T \rightarrow 0$), the conductance through the dot is given by Eq. (62) as a superposition of transmission curves $T(E_F - E_\gamma)$, where γ corresponds to an open channel for the transport.

In experiments G and therefore T is probed at different energies by varying the voltage of an additional plunger gate. In case of lateral tunneling, this additional gate is a top gate^{17,38} and, in the case of vertical tunneling, it is a side gate³⁹. We use the following idealization for the total potential in presence of a varying gate voltage: The external potential created by the charges at the gate is screened out completely in the heavily doped contacts ($|z| > d$) so that the total potential and E_F remain unchanged. In the scattering area ($|z| < d$) the total potential can be idealized for small variations of the gate voltage as a varying potential energy offset eU_g , so that $V(z) = V(z) - eU_g$. As shown in Fig. 3 the transmission probability of the double barrier system depends on the gate potential U_g and therefore the conductance G varies with U_g .

As illustrated in Fig. 3 for small energies ($E < \max[V(z)]$) the transmission is generally small and may have some isolated peaks at E_i . The peak position depends on the total potential energy experienced by electrons and therefore $E_i = E_i(U_g)$. The line shape of a transmission peak is deduced from Eq. (70) and is given by

$$T(E) = (S(E))_{12}^2, \quad T_{bg} \frac{[e + \operatorname{Re}(q)]^2 + [\operatorname{Im}(q)]^2}{e^2 + 1}; \quad (73)$$

where $T_{bg} = (S_{bg})_{12}^2$ is the background transmission. The right hand side of Eq. (73) is a Fano distribution with a complex asymmetry parameter²⁸

$$q = i \frac{S(E_i)_{12}}{S_{bg}} \frac{1}{S_{bg}}; \quad (74)$$

As shown in Fig. 3 the Fano approximation for the line shape of the transmission gives a very good description even for the asymmetric peaks as long as the peaks are quasi-isolated. The background matrix S_{bg} in Eq. (70) is often assumed to be absent, leading to a symmetrical Wigner-Breit line shape of the transmission³⁷, but it is obviously that such a description fails in the case of an asymmetric peak as the second peak in Fig. 3.

If the Fermi energy is smaller than the maximum of the barriers and if the external voltages U_g are quite small, only the isolated peaks participate to the transport. According to Eq. (62) the conductance has a maximum each time the transmission of an open channel has a peak,

$$E_{i0}(U_0) = E_F - E_\gamma^0; \quad (75)$$

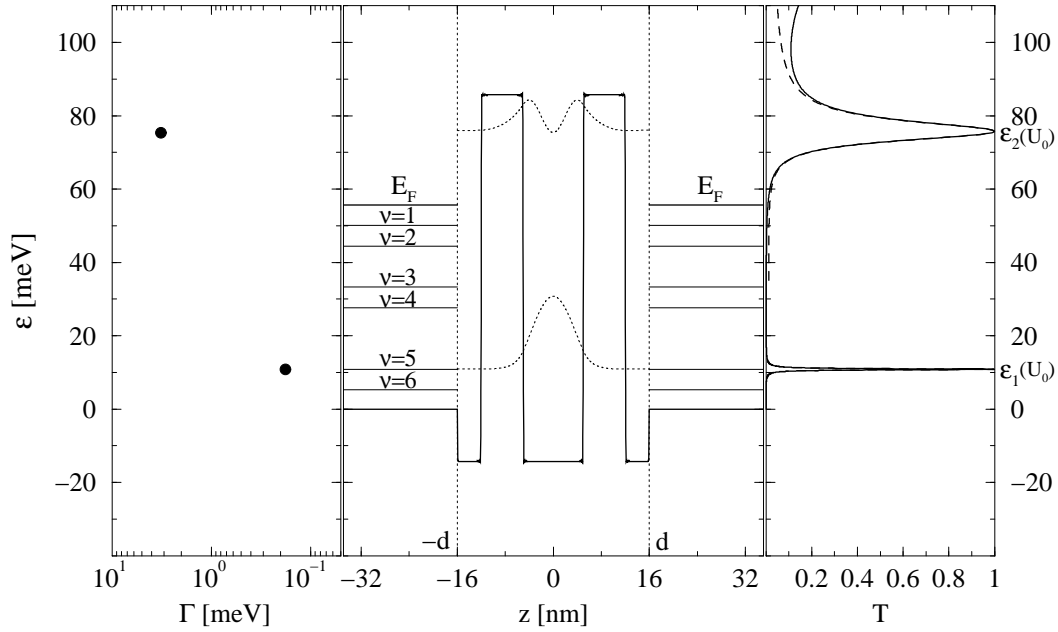


FIG. 3: Middle: Total potential energy of a double-barrier structure, $V(z) = eU_g$, for a value of the gate voltage which corresponds to a maximum in conductance, $U_g = U_0 = 14.28 \text{ mV}$. The potential steps of height eU_0 at $\pm z = d$ ($d = 16 \text{ nm}$) result from the voltage applied to the plunger gate. In dotted lines the wave functions $\psi^{(i)}$ at the resonant energies $\epsilon_i(U_0)$, $i = 1, 2$. The energies E_F and E_2 (solid lines) are drawn in the contact regions, where E_2 , $i = 1, 6$ correspond to an infinite 2D quantum well with the dimensions $16 \text{ nm} \times 16 \text{ nm}$. Left: Positions of the resonance poles of the S matrix in the complex energy plane. Right: Transmission $T(U_0; \epsilon)$ vs. energy calculated for the scattering potential energy $V(z) = eU_0$: numerical calculation (solid lines) and Fano approximation (dashed lines).

Thus, to each conductance maximum at $U_g = U_0$ a pair index $(i_0; i_0)$ is assigned, where i_0 is the channel index and i_0 the number of the maximum in the curve $T(U_0; \epsilon)$. As shown in Fig. 3 each index i_0 can be associated with a pole of the scattering matrix and we can conclude that a maximum in conductance is characterized by a resonant channel i_0 and a resonant pole of the S matrix, ϵ_{i_0} . On this basis one can split the contribution to the conductance into a coherent resonant part,

$$G_C(U_g) = \frac{2e^2}{h} T(U_g; E_F, E_2^{i_0}); \quad (76)$$

and a slowly varying noncoherent part

$$G_{NC}(U_g) = \frac{2e^2}{h} \sum_{i_0} T(U_g; E_F, E_2^{i_0}); \quad (77)$$

in which the absolute squares of the transmission coefficients are added without phase information. In the above expression only the contributions of the open channels are counted. Fig. 4 illustrates the conductance through the dot and its coherent and noncoherent contributions around a maximum at $U_g = U_0$.

In case of a narrow conductance peak the R-matrix representation of the scattering matrix allows for obtaining an explicit dependence $G = G(U_g)$ in the vicinity of the maximum, $U_g = U_0 + U$. By the transformation $V(z) \rightarrow V(z) - eU_g$ the Wigner-Eisenbud energies ϵ_1 [Eq. (15)] become $\epsilon_1 - eU_g$ but the Wigner-Eisenbud functions ϵ_1 remain unchanged. Then, according to Eq. (30) the matrix $(U_g;)$ can be approached by $(U_0; + e U)$. Thus, from Eq. (29) follows that $T(U_g;) = T(U_0; + e U)$. Inserting condition (75) in the above relation we obtain the coherent and noncoherent contributions to the conductance around the maximum,

$$G_C(U_g) = \frac{2e^2}{h} T(U_0; i_0 + e U); \quad (78)$$

and

$$G_{NC}(U_g) = \frac{2e^2}{h} \sum_{\epsilon_0}^X T(U_0; i_0 + E_{\epsilon_0}^0 - E_{\epsilon_0} + e U); \quad (79)$$

respectively, where i_0 is the position of the i_0 -th transmission maximum for the potential energy $V(z) - eU_0$.

Using Eq. (73) the coherent contribution to the conductance in the vicinity of the resonance is obtained as a Fano function with the complex asymmetry parameter q defined by (74),

$$G_C(U_g) = G_{bg} \frac{[e + \text{Re}(q)]^2 + [\text{Im}(q)]^2}{e^2 + 1}; \quad (80)$$

Here $e = 2e(U_g - U_0) = i_0$ is a function of the plunger gate potential U_g , the resonance position U_0 and the resonance width i_0 calculated as the imaginary part of the i_0 -th pole of the scattering matrix for the potential $V(z) - eU_0$. The background coherent contribution is related to the background transmission through $G_{bg} = (2e^2/h)T_{bg}$.

As shown in Fig. 4 the noncoherent part of the conductance varies slowly inside the resonance domain and we can expand this function in a Taylor series for $U_g - U_0$. One obtains

$$G_{NC}(U_g) = \frac{2e^2}{h} \sum_{\epsilon_0}^X T(U_0; i_0 + E_{\epsilon_0}^0 - E_{\epsilon_0}) + e U \frac{2e^2}{h} \sum_{\epsilon_0}^X \frac{dT}{d\epsilon} \Big|_{\epsilon = i_0 + E_{\epsilon_0}^0 - E_{\epsilon_0}}; \quad (81)$$

As illustrated in Fig. 4, Eqs. (80) and (81) provide a very good description of the two contributions to the conductance of the dot. If the overlap of the peaks is very small, the noncoherent contribution to the conductance can be considered even as constant²⁸.

We can conclude that the most general form of a conductance profile is a Fano line with a complex asymmetry parameter superposed on a linear function which usually increases the asymmetry of the profile. The Fano function arises from the coherent superposition of contributions to the S-matrix coming from different poles and the linear function is determined by the nonresonant channels whose contributions add noncoherently. Therefore we have demonstrated that the asymmetry of the profile in conductance does not necessarily involve the coupling between two different channels as in the usual scenario to explain Fano resonances³⁴. In addition, the asymmetry of the conductance profile is not necessarily the asymmetry of the transmission peak.

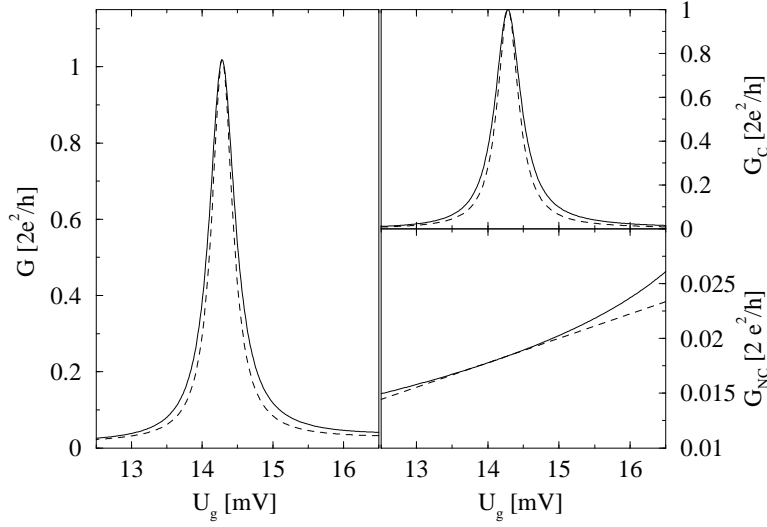


FIG. 4: Left: Conductance vs. gate voltage around the maximum at $U_0 = 14.28$ mV: complete calculation Eq. (62) (solid line) and approximate value $G = G_C + G_{NC}$ given by Eqs. (80) and (81) (dashed line). Right upper part: Coherent contributions to the conductance around maximum: complete calculation Eq. (76) (solid line) and Fano approximation Eq. (80) (dashed line). Right lower part: Noncoherent contributions to the conductance around maximum: complete calculation Eq. (77) (solid line) and linear approximation Eq. (81) (dashed line).

In our theory of the resonant transport all parameter necessary to describe the conductance profile can be calculated microscopically and we can evaluate separately the coherent and the noncoherent parts of the conductance. The two contributions arise naturally in our formalism of the coherent transport through open systems. We do not exclude the existence of the incoherent processes in nanostructures which can contribute to the conductance, but we have found that the coherent processes contribute coherently and noncoherently to the conductance.

B. CAPACITANCE OF QUANTUM MIS-TYPE HETEROSTRUCTURES

Further, we analyze a quantum MIS (metal-insulator-semiconductor)-type heterostructure. The considered AlAs/GaAs structure⁴² consists of a sequence of layers grown on a GaAs bulk material given by, first, n-GaAs layer as a back contact, second, intrinsic GaAs layer as a spacer, third, a short period Al_xGa_{1-x}As=GaAs superlattice as a blocking barrier and finally a metallization as a top gate. The band structure, Fig. 5, resulting from the self-consistent calculations in the Hartree approximation^{30,40} shows for large enough positive gate voltages U_g a potential well at the interface between the GaAs spacer and the blocking barrier, where a field induced two-dimensional electron gas (2DEG) develops.

The blocking barrier is now assumed to suppress charge transfer completely and we consider the limit of small frequencies. Then, the tunnel capacitor in Fig. 5 becomes equivalent to a simple plate capacitor⁴³. The charge corresponding to the left plate is distributed in the region $-d < z < z_0$ (see. Fig. 5) and can be evaluated using Gauss' law,

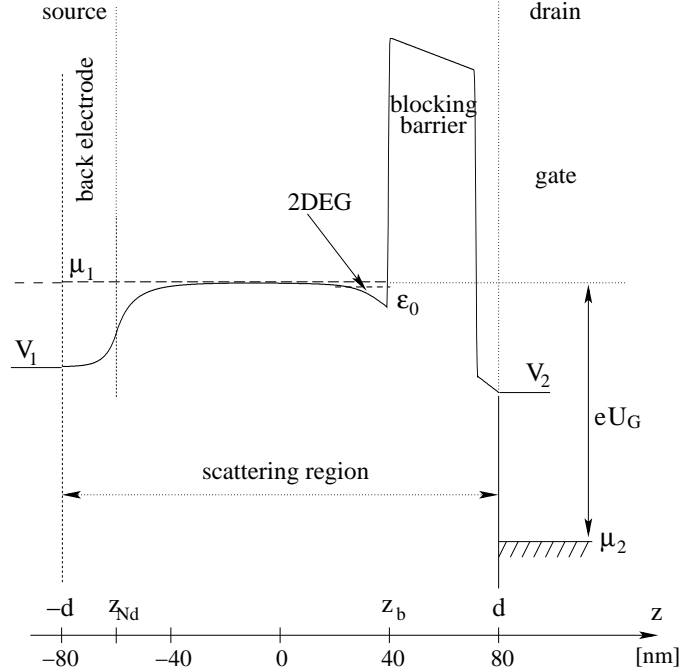


FIG. 5: Band diagram from self-consistent calculation^{30,40} for the MIS-type AlGaAs/GaAs heterostructure. The structure parameters correspond to the experiments in Ref.⁴².

$Q_1 = \int_{-d}^{z_b} S (\partial V / \partial z) dz$ ($z = z_b$). Here z_b is the interface between the barrier and the GaAs-spacer layer, S is the area of the sample, and ϵ_0 is the dielectric permittivity. The top gate of the structure acts as the right plate of the capacitor and the charge on it is $Q_2 = -Q_1$. The capacitance is then readily found as

$$C = \frac{\partial Q_1}{\partial U_g} = \frac{\partial Q_2}{\partial U_g} : \quad (82)$$

In Fig. 6 we compare the experimental C - V -curve⁴² with the results of our model³⁰. For the numerical calculations, we use the parameters corresponding to the experiments in Ref.⁴². Because the work function of the metal contact is not precisely known we shift the theoretical voltage scale U_g with respect to the experimental one U_G ($U_G = 0.701V + U_g$), so that the centers of the steps coincide. $U_g = 0$ corresponds to the flat band configuration. It can be seen that for such a system the C - V curve takes the form of a broadened step located between a low voltage, $U_g < U_-$, and a high-voltage, $U_g > U_+$, plateau. We define the gate voltage U_c at the center of the step by $d^2C/dU_g^2 = 0$; U_- and U_+ correspond to the gate voltages where dC/dU_g takes half of its maximum value.

To understand the variation of the capacitance with the gate voltage in the step domain we perform the pole analysis. For the scattering potential of the biased structure, Fig. 7 illustrates the pole energies with the real part in the energy domain of the occupied states and the scattering functions at the resonance energies corresponding to these poles. This figure shows that there are two types of poles: the first one is associated with the scattering states of the electrons confined in the region close to the back contact. The corresponding charge distribution varies very slowly with the applied bias^{30,42}. Therefore, these resonances do not play any role in the capacitance variation with U_g . The second type of poles, with a

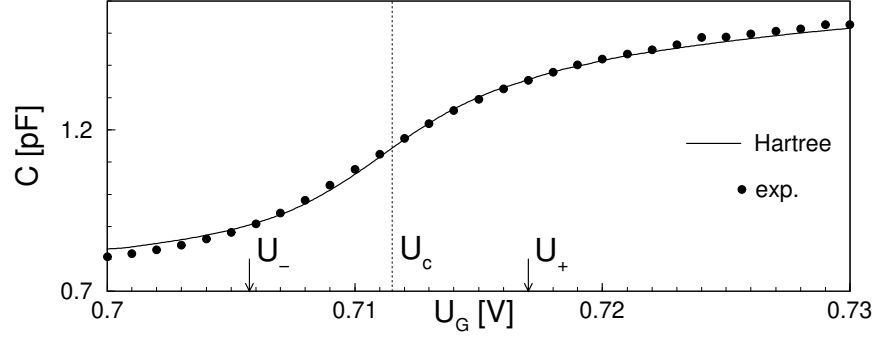


FIG. 6: C-V curve, experimental data (filled circles)⁴² and numerical calculation (solid line).

smaller imaginary part, corresponds to the states of the electrons localized at the interface between the GaAs spacer layer and the blocking barrier. In our case there is a single pole

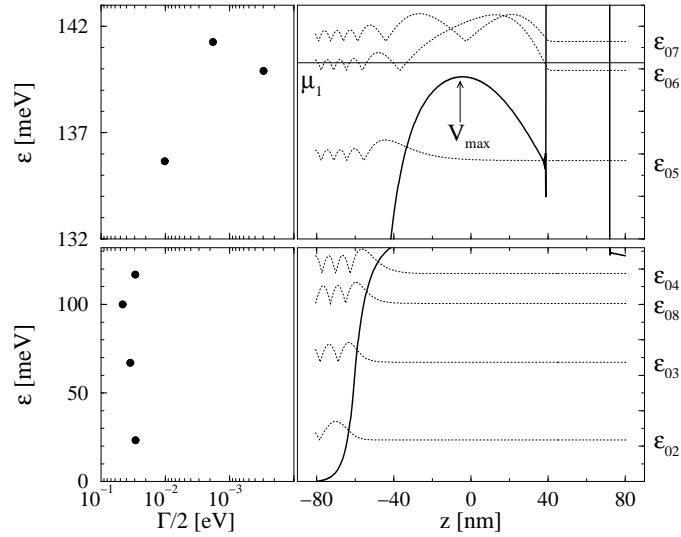


FIG. 7: Left: Position of the resonance poles in the complex energy plane determined by Eq. (68). Right: Potential energy $V(z)$ (solid line) for $U_g = 16$ mV and $j^{(1)}(z)$ at the resonance energies (dotted line). The upper plots present in detail an energy domain around ϵ_1 . V_{\max} marks the height of the wide and shallow barrier which is formed between the back contact and the blocking barrier, $V_{\max} = \max_{d < z < z_b} [V(z)]$.

with the resonance energy below the chemical potential μ_1 and for which $j^{(1)}(z)$ has a maximum in the region of the potential quantum well³⁰. We denote the complex energy of this pole by $\epsilon_0 = \epsilon_0 - i\Gamma/2$. The imaginary part of this pole is smaller than that of the other poles and smaller than the gap between two adjacent resonance energies. The charge accumulated in the quantum well varies strongly with U_g and, consequently, the changes of the capacitance can be directly connected to the resonances of the second type. A quantity which gives information about the contributions of different poles to the charge accumulated in the system is the probability distribution $P_s(\epsilon)$ [Eq. 55]. In Fig. 8, $P_1(\epsilon)$ is plotted for

two values of the applied bias: $U_g = 11 \text{ mV}$, corresponding approximately to the center of the capacitance step and $U_g = 25 \text{ mV}$, corresponding to the high voltage plateau of the capacitance curve (Fig. 6). In the middle part of Fig. 8 the resonance energy ϵ_0 and the energies $\epsilon_{0 \pm 2}$ are presented as a function of U_g together with the energy of the maximum of $P_1(\epsilon)$, ϵ_{max} , and the energies where $P_1(\epsilon)$ takes half the maximum value. For comparison the chemical potential and the height of the wide and shallow barrier which is formed between the back contact and the blocking barrier, $V_{\text{max}} = \max_{d \leq z \leq z_b} [V(z)]$, are also plotted. In this

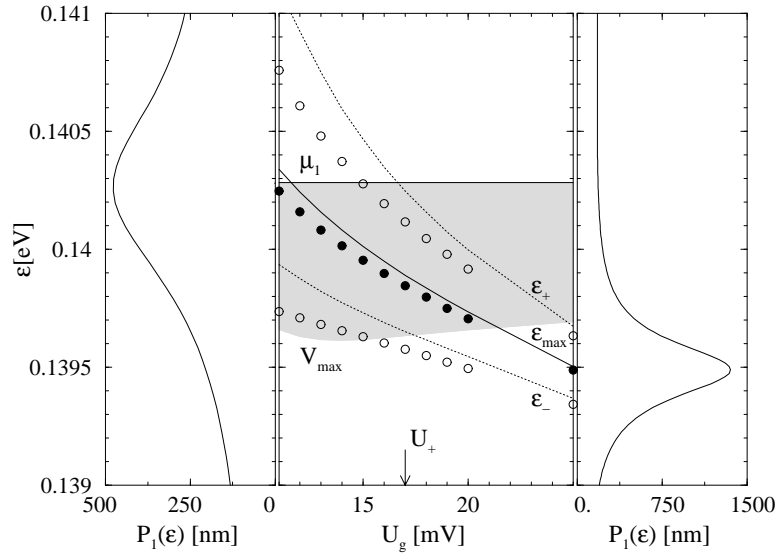


FIG. 8: Left part: Probability distribution $P_1(\epsilon)$ around the resonance energy ϵ_0 for $U_g = 11 \text{ mV}$. Right side: Probability distribution $P_1(\epsilon)$ around the resonance energy ϵ_0 for $U_g = 25 \text{ mV}$. Middle part: The energy ϵ_{max} of the maximum of $P_1(\epsilon)$ (solid line), and the energies at which $P_1(\epsilon)$ takes half the maximum value (dotted lines), the resonant energies ϵ_0 (filled circles) and the energies $\epsilon_{0 \pm 2}$ (circles). Shaded area: energies which correspond to the classically allowed channel ($\epsilon_1 > V_{\text{max}}$).

situation V_{max} is below the chemical potential μ_1 and a classically allowed channel for the electrons is opened. For small positive values of U_g the maximum of $P_1(\epsilon)$ lies in this channel. With increasing U_g a potential quantum well is formed at the interface between the spacer layer and the blocking barrier and $P_1(\epsilon)$ has a sharp maximum which is located in an energy range with no classically allowed connection between the electrons in the quantum well and the back contact. So we can conclude that for positive values of U_g $P_1(\epsilon)$ has a pronounced maximum centered on ϵ_0 with a well defined width ($\epsilon_{0 \pm 2}$). The charge accumulation in the field induced quantum well of the quantum MIS type semiconductor is characterized mainly by the resonance associated with the pole ϵ_0 ($i=2$). This resonance changes its character from an intermediate resonance to a quasibound state. For small applied biases ($U < U_g < U_+$) this resonance has the character of an intermediate resonance³⁰: i) its energy lies in the classically allowed range (Fig. 8, middle part) and, therefore, is a Fabry-Perot type resonance; ii) it is located in the space between the contact and the region where an isolated 2DEG is formed at large values of V_g (Fig. 3b.) Ref.³⁰; iii) its shape is strongly asymmetric (Fig. 8, left part). With increasing U_g the intermediate resonance turns into a quasibound state which, in contrast to the intermediate resonance, is connected to the

back contact only via the tunneling effect. The resonance line of $P_1(\epsilon)$ narrows and tends to become symmetric (Fig. 8, right part). The excellent quantitative agreement between the experimental data and the modeled capacitance curve, Fig. 6, demonstrates that the electronic states, which are important for the capacitance step and the subsequent high-voltage plateau are derived from a single resonance.

V. CONCLUSIONS

We first analyze the electronic scattering states in semiconductor nanostructures and, on this basis, the transport properties of the electron gas: conductance and capacitance. The considered systems are mesoscopic and the transport is supposed ballistic. The physics of these systems is often dominated by resonances which are broadened due to the open character of the systems. We develop a theory of resonant transport in semiconductor nanostructures valid for all coupling regimes between the quantum system and contacts, i.e. for open systems as well as for almost-closed quantum systems. To separate weakly from strongly energy dependent contributions on the scale of the width of the resonance we employ a representation of the S matrix in terms of the R matrix. We find a simple procedure to determine the poles of the S matrix in the complex energy plane, which gives the position and the width of the resonances. Numerical results show the remarkable accuracy of our procedure which is applied to a great variety of resonances types: quasibound states, Fowler-Nordheim, and Fabry-Perot resonances. In case of separate resonances, the linearization of the weakly energy dependent part in S matrix yields an analytical expression of the line shape which is a Fano profile with a complex asymmetry parameter. The resonant theory of transport is applied to study the conductance through a quantum dot embedded in a quantum wire and the capacitance of a 2DEG formed at the interface between the spacer layer and the blocking barrier in a MIS-type semiconductor heterostructure.

APPENDIX A: ORTHOGONALITY OF THE SCATTERING FUNCTIONS

The main aim of this section is to demonstrate Eq. (35) using the expressions (10), (11), and (18) of the scattering functions and the relation (29) between the S and the R matrix. For an effective calculation of the scalar product between $\psi^{(s)}(\epsilon; z)$ and $\psi^{(s^0)}(\epsilon^0; z)$ it is necessary to split the integral into two contributions, the first one given by the scattering domain and the second one given by the lateral regions (outside the scattering domain),

$$\int_{-1}^1 dz \psi^{(s)}(\epsilon; z) \psi^{(s^0)}(\epsilon^0; z) = I_{ss^0}^{\text{int}}(\epsilon; \epsilon^0) + I_{ss^0}^{\text{ext}}(\epsilon; \epsilon^0); \quad (\text{A } 1)$$

Further we are interested in evaluating the above integral only in the cases in which the energies ϵ and ϵ^0 are in the same domain: $\epsilon; \epsilon^0 > V_M$ or $V_m < \epsilon; \epsilon^0 < V_M$. If the two energies belong to different domains, the corresponding eigenfunctions are orthogonal due to the selfadjointness of the Hamilton operator in Eq. (6) and consequently Eq. (35) is fulfilled.

On integrating over the lateral regions such terms occur as

$$\int_a^1 dz e^{i(k - k^0)z} = e^{i(k - k^0)a} iP \frac{1}{k - k^0} + \dots (k - k^0); \quad (\text{A } 2)$$

The integral in the above expression of $I_{ss^0}^{int}(\vec{k}; \vec{k}^0)$ can be easily calculated if the R functions are replaced by their definition (22) and the orthogonality condition of the Wigner-Eisenbud functions [Eq. (16)] is used. After that a very simple trick,

$$\frac{1}{(\vec{k} - \vec{k}^0)(\vec{k}^0 - \vec{k}^1)} = P \frac{1}{\vec{k} - \vec{k}^0} - \frac{1}{\vec{k}^0 - \vec{k}^1} + \frac{1}{\vec{k} - \vec{k}^1}; \quad (A 9)$$

where the Cauchy principal part is defined by Eq. (A 3), allows us to write

$$\begin{aligned} & \int_{\vec{k}^0}^{\vec{k}^1} d\vec{k} R(\vec{k}; (\vec{k}^1 - \vec{k}^0)d; z) R(\vec{k}^0; (\vec{k}^1 - \vec{k}^0)d; z) \\ &= \frac{\hbar^2}{2m} \frac{1}{2d} P \frac{1}{\vec{k} - \vec{k}^0} R(\vec{k}^0; (\vec{k}^1 - \vec{k}^0)d; (\vec{k}^1 - \vec{k}^0)d) - R(\vec{k}; (\vec{k}^1 - \vec{k}^0)d; (\vec{k}^1 - \vec{k}^0)d) : \end{aligned} \quad (A 10)$$

Inserting Eq. (A 10) in Eq. (A 8) we obtain

$$I_{ss^0}^{int}(\vec{k}; \vec{k}^0) = M_{ss^0}(\vec{k}; \vec{k}^0); \quad (A 11)$$

Using the expressions of the integrals inside and outside the scattering region [Eqs. (A 11) and (A 5), respectively] the orthogonality condition [Eq. (35)] of the scattering functions follows from Eq. (A 1).

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